| Manufacturers | Infineon Technologies Corporation |
| :--- | :--- |
| Package/Case | TO-252 |
| Product Type | Transistors |
| RoHS |  |
| Lifecycle |  |



Images are for reference only

Please submit RFQ for IPD640N06LG or Email to us: sales@ovaga.comWe will contact you in 12 hours.
RFQ

## General Description

IPD640N06LG is a specific model number for a power MOSFET semiconductor device. Here are some details on this device:

## Features

N-channel MOSFET

Maximum drain-source voltage of 60 V

Continuous drain current of 120A

Low on-resistance (0.004 ohms)

Fast switching speed

## Application

Power management in DC-DC converters

Motor control

Power supplies

Lighting systems

Battery charging circuits

TO-252-3 package


## Related Products



## IPP60R070CFD7

Infineon Technologies Corporation
TO-220-3

## IPG20N04S4-12

Infineon Technologies Corporation
TDSON-8


## IPB180N06S4-H1

Infineon Technologies Corporation
PG-TO263-7-3

IPW65R080CFD
Infineon Technologies Corporation
TO-247


IPD25N06S4L-30
Infineon Technologies Corporation
PG-TO252-3


IPP60R074C6
Infineon Technologies Corporation TO-220-3


IPD180N10N3G
Infineon Technologies Corporation TO-252


IPD70R1K4P7S
Infineon Technologies Corporation
TO252-3

